



**WANSEMI**  
万芯半导体

**WP8205C**

# **Enhancement Mode N-Channel Power MOSFET**

SOT23-6/NMOS/16V/ $\pm 12$ V/0.55V/4A/19m $\Omega$

Rev0.8

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## 16V, 19mΩ, 4A, N-Channel MOSFET

### 1.Features

- ◆ High Power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

V <sub>DS</sub> Typ.	R <sub>DS(on)</sub> Typ.	I <sub>D</sub> Max.
16V	19mΩ @ 4.5V	4A
	24mΩ @ 2.5V	

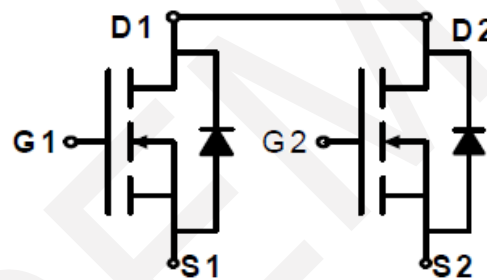
### 2.Applications

- ◆ Battery Protection
- ◆ Battery Powered Systems
- ◆ Power Management in Notebook Computer
- ◆ Portable Equipment



Pin Description

SOT23-6



Schematic Diagram

### 3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP8205C	8205A	SOT23-6	3,000	180,000

### 3.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V <sub>DSS</sub>	16	V
Gate to Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	4	A
Drain Current (Pulse)	I <sub>DM</sub>	30	A
Maximum Power Dissipation	P <sub>D</sub>	1.5	W
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

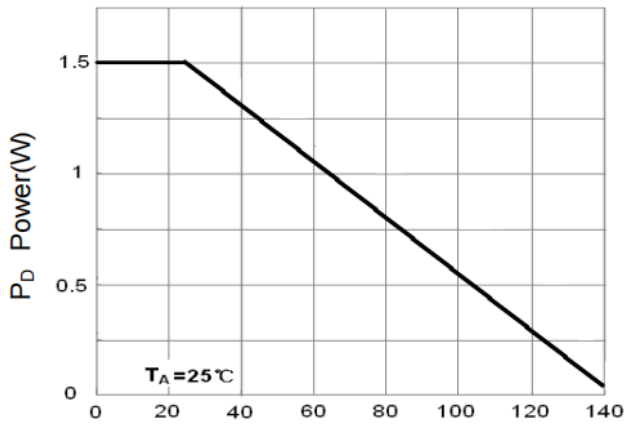
**4. Electrical Characteristics at Ta=25°C (Note 2)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	16	18	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = 250\mu A$	0.4	0.55	1.2	V
Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 4A, V_{GS} = 4.5V$	-	19	24	m $\Omega$
		$I_D = 3A, V_{GS} = 2.5V$	-	24	30	m $\Omega$
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 10V,$ Frequency=1.0MHz	-	1150	-	pF
Output Capacitance	$C_{oss}$		-	185	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	145	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 4A,$ $V_{GS} = 4.5V, R_{GEN} = 6\Omega$	-	6	-	ns
Turn-ON Rise Time	$t_r$		-	13	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	52	-	ns
Turn-ON Fall Time	$t_f$		-	16	-	ns
Total Gate Charge	$Q_g$	$V_{DS} = 10V,$ $V_{GS} = 4.5V,$ $I_D = 4A$	-	15	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.2	-	nC
Diode Forward Voltage	$V_{SD}$	$I_S = 4A, V_{GS} = 0V$	-	0.9	1.2	V

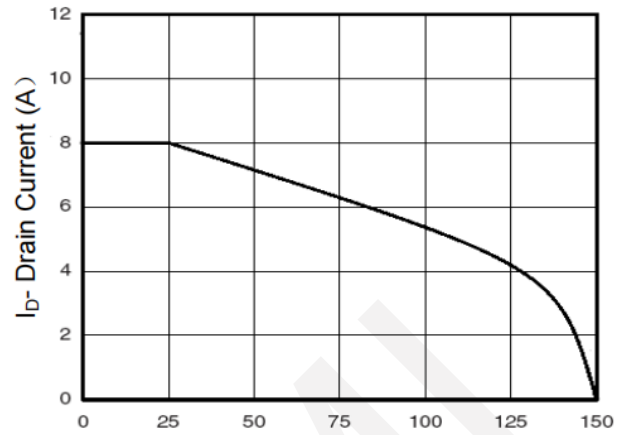
Note 2: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



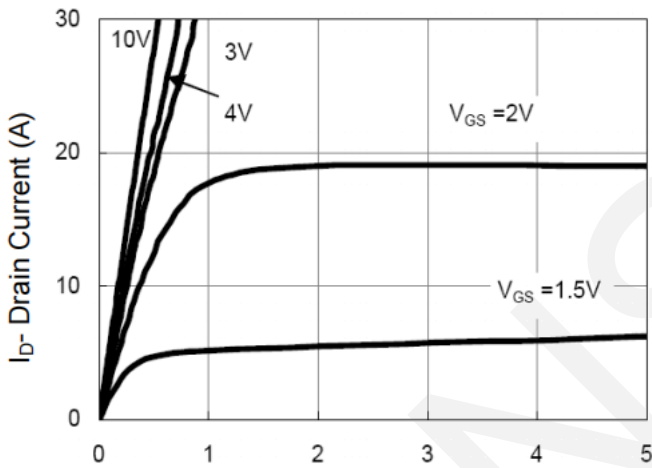
### 5. Typical electrical and thermal characteristics



$T_J$ -Junction Temperature( $^{\circ}C$ )  
Power Dissipation

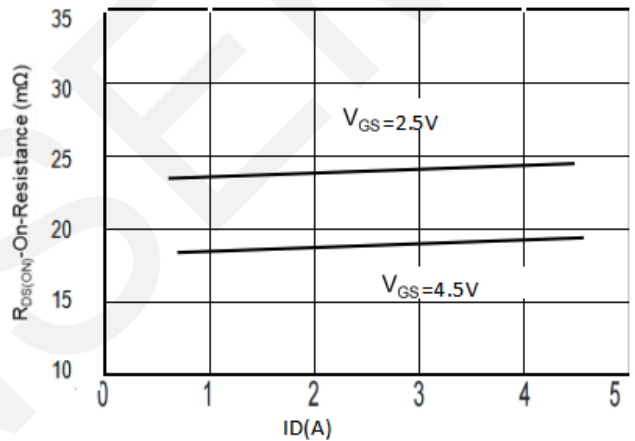


$T_J$ -Junction Temperature( $^{\circ}C$ )  
Drain Current

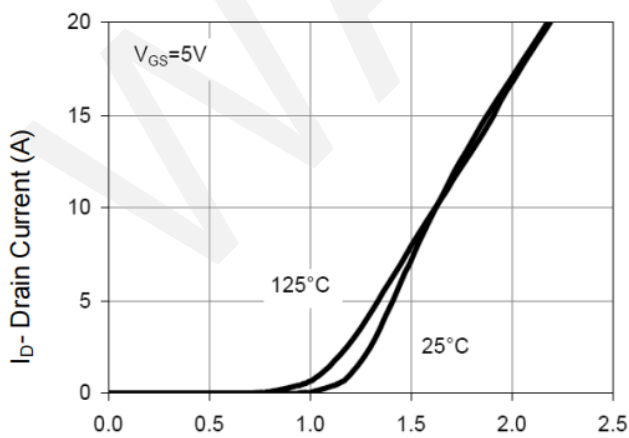


$V_{DS}$  Drain-Source Voltage (V)

Output Characteristics

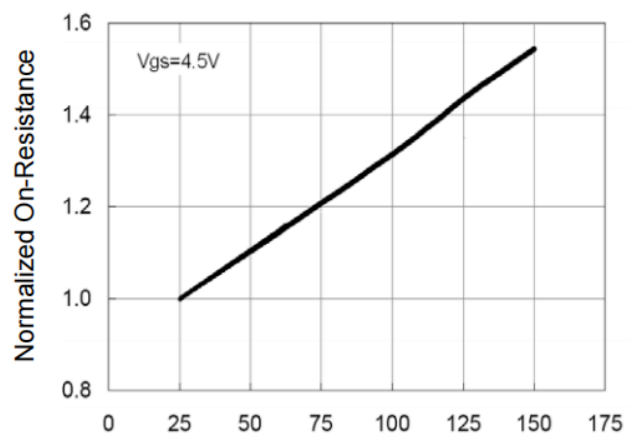


Drain-Source On-Resistance



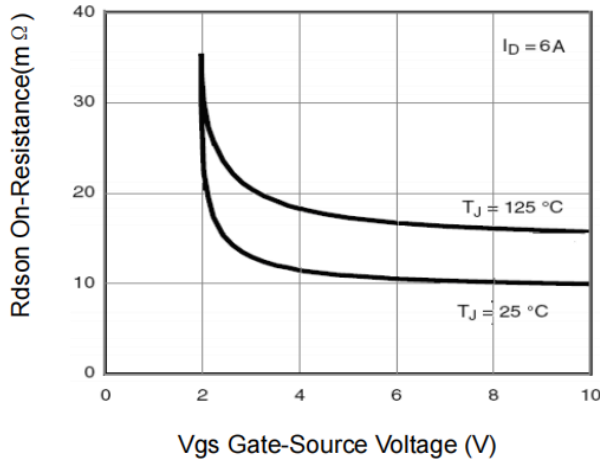
$V_{GS}$  Gate-Source Voltage (V)

Transfer Characteristics

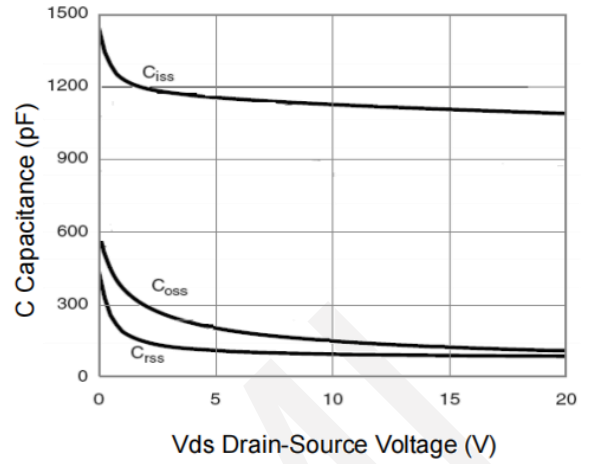


$T_J$ -Junction Temperature( $^{\circ}C$ )

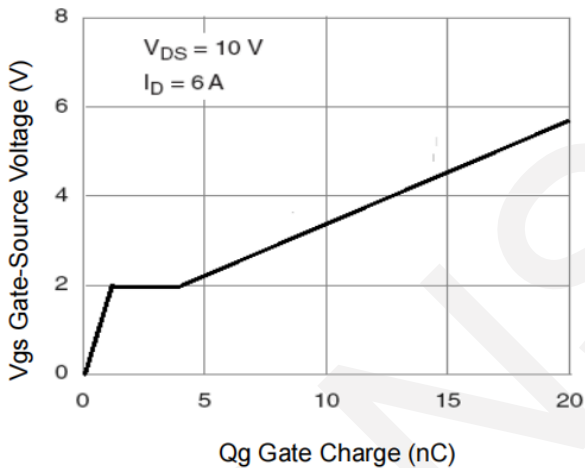
Drain-Source On-Resistance



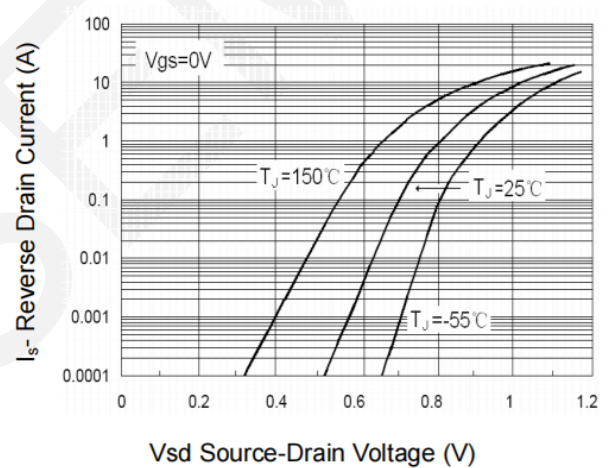
Rdson vs Vgs



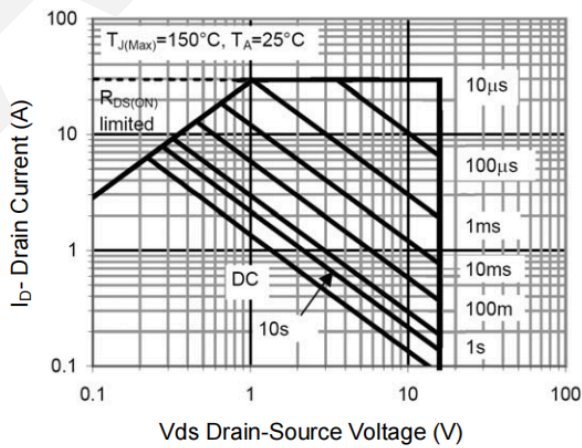
Capacitance vs Vds



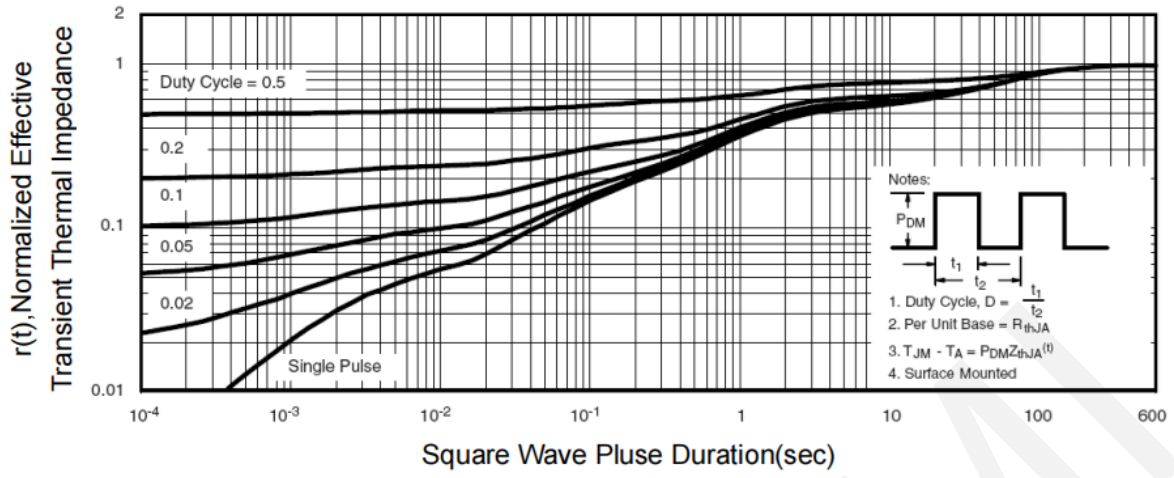
Gate Charge



Source-Drain Diode Forward



Safe Operation Area

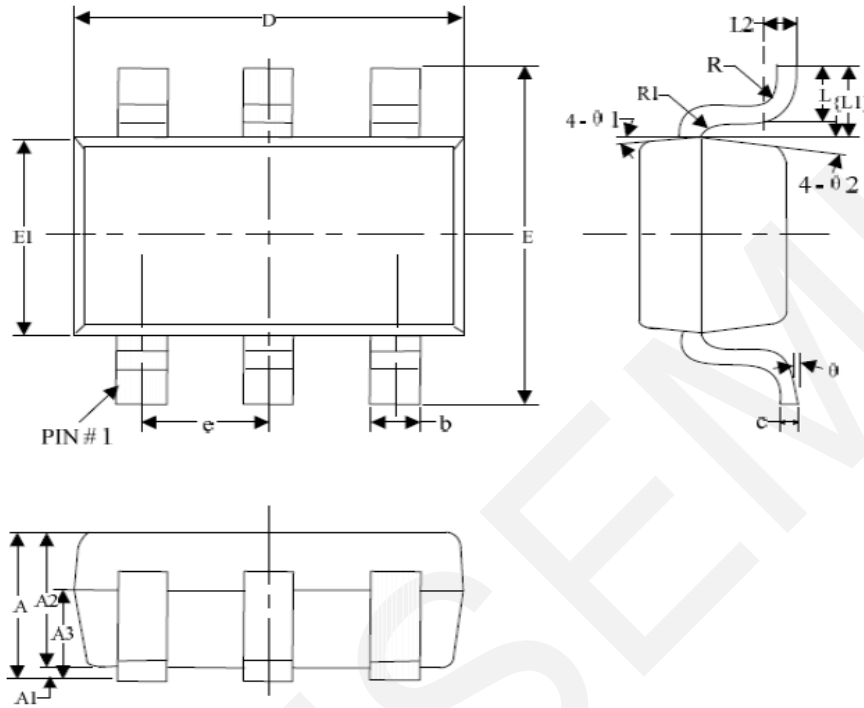


Normalized Maximum Transient Thermal Impedance



**6.Package Dimensions**

**SOT23-6**



**Dimensions (unit: mm)**

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	-	-	1.30	e	0.85	0.95	1.05
A1	0	-	0.15	L	0.35	0.45	0.60
A2	0.90	1.10	1.30	L1	0.59REF		
A3	0.60	0.65	0.70	L2	0.25BSC		
b	0.39	-	0.49	R	0.05	-	-
c	0.12	-	0.19	R1	0.05	-	0.02
D	2.85	2.95	3.15	θ	0°	-	8°
E	2.60	2.80	3.00	θ1	3°	5°	7°
E1	1.55	1.65	1.75	θ2	6°	8°	10°

## 7.Important Notice

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